IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) An apparatus for vaporizing a solid precursor, comprising:

a housing having an interior volume and an inlet for receiving a carrier gas, wherein the interior volume is configured to receive a solid chemical precursor; and

at least two surfaces contained in the housing and having the solid chemical precursor applied thereto, wherein each of the at least two surfaces comprise a heating element and are spaced to allow flow of the carrier gas therebetween.

2. (Original) The apparatus of claim 1, wherein the apparatus further comprises an outlet operably connected to a reaction chamber of a deposition chamber.

3. (Previously presented) The apparatus of claim 2, wherein the at least two surfaces are selected from the group consisting of a baffle, a rod, a mesh, and a grating.

4. (Previously presented) The apparatus of claim 1, wherein the at least two surfaces have a form selected from the group consisting of an s-shape, a linear shape and a cone shape.

5. (Currently Amended) The apparatus of claim 3, wherein the at least two surfaces comprise stainless steel ~~and~~ or ceramic.

6. (Previously presented) The apparatus of claim 2, wherein the deposition chamber is selected from the group consisting of an atomic layer deposition chamber, a chemical vapor deposition chamber, and an evaporative coating chamber.

7. (Original) The apparatus of claim 6, wherein the solid precursor includes a tantalum-containing precursor or a tungsten-containing precursor.

8. (Currently Amended) An apparatus for vaporizing a solid precursor, comprising:

a housing having an interior volume, wherein the interior volume is configured to receive a solid chemical precursor;

an inlet for receiving a carrier gas;

an outlet for delivering the carrier gas and a vaporized solid precursor, the vaporized solid precursor originating from the solid chemical precursor;

a first wall to support the inlet;

at least two surfaces contained in the housing and spaced to allow passage of the carrier gas, the at least two surfaces having the solid precursor applied thereto; and

a heating member contained in each of the at least two surfaces.

9. (Original) The apparatus of claim 8, wherein the outlet is operably connected to a reaction chamber of a deposition chamber.

10. (Previously presented) The apparatus of claim 9, wherein the at least two surfaces are selected from the group consisting of a baffle, a rod, a mesh, and a grating.

11. (Cancelled)

12. (Previously presented) The apparatus of claim 9, wherein the at least two surfaces have a form selected from the group consisting of an s-shape, a linear shape and a cone shape.

13. (Previously presented) The apparatus of claim 12, wherein the at least two surfaces comprise stainless steel or ceramic.

14. (Previously presented) The apparatus of claim 9, wherein the deposition chamber is selected from the group consisting of an atomic layer deposition chamber, a chemical vapor deposition chamber, and an evaporative coating chamber.

15. (Original) The apparatus of claim 14, wherein the solid precursor includes a tantalum-containing precursor or a tungsten-containing precursor.

16. (Currently Amended) An apparatus for vaporizing a solid tantalum-containing precursor, comprising:

a housing comprising an interior volume having an inlet for receiving a carrier gas and an outlet for delivering the carrier gas and a vaporized solid precursor, wherein the vaporized solid precursor originates from the solid tantalum-containing precursor;

at least two surfaces contained in the housing and having the solid tantalum-containing precursor applied thereto, wherein the at least two surfaces are configured to heat the solid tantalum-containing precursor and are spaced to allow passage of the carrier gas therebetween; and

at least one heating member contained in at least one wall of the housing wherein the outlet is operably connected to a reaction chamber of a deposition chamber.

17. (Previously presented) The apparatus of claim 16, wherein the at least two surfaces are independently selected from the group consisting of a baffle, a rod, a mesh and a grating.

18. (Cancelled)

19. (Previously presented) The apparatus of claim 16, wherein the deposition chamber is selected from the group consisting of an atomic layer deposition chamber, a chemical vapor deposition chamber, and an evaporative coating chamber.

20. (Cancelled)

21. (Currently Amended) An apparatus for vaporizing a solid tantalum-containing precursor, comprising:

a housing having an interior volume configured to receive the solid tantalum-containing precursor;

an inlet for receiving a carrier gas;

at least two baffles in thermal communication with the solid tantalum-containing precursor, the at least two baffles having the solid tantalum-containing precursor applied thereto and spaced to allow passage of the carrier gas;

an outlet for delivering the carrier gas and a vapor originating from the solid tantalum-containing precursor, the outlet operably connected to an atomic layer deposition chamber; and

a heating member contained in each of the at least two baffles.